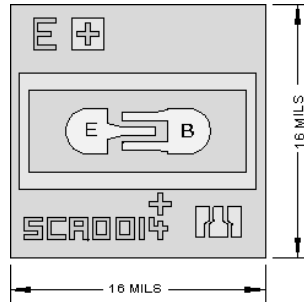


**Chip Type 2C4261**  
**Geometry 0014**  
**Polarity PNP**

**Generic Packaged Parts:**  
**2N4260, 2N4261**



[Request Quotation](#)

Chip type **2C4261** by Semicoa Semiconductors provides performance similar to these devices.

**Product Summary:**

**APPLICATIONS:**

Designed for low voltage, low gain RF amplifier applications.

**Part Numbers:**

2N4261, 2N4261UB, 2N4260, 2N4260UB, SD4261, SD4261F, SQ4261, SQ4261F

**Features: Special Characteristics**

$f_t = 1.8 \text{ GHz (typ) at } 10 \text{ mA/10V}$

Mechanical Specifications		
Metallization	Top	Al - 12 kÅ min.
	Backside	Au - 6.5 kÅ nom.
Bonding Pad Size	Emitter	2.1 mils x 2.1 mils
	Base	2.1 mils x 2.1 mils
Die Thickness	8 mils nominal	
Chip Area	16 mils x 16 mils	
Top Surface	Silox Passivated	

Electrical Characteristics				
$T_A = 25^\circ\text{C}$				
Parameter	Test conditions	Min	Max	Unit
$BV_{CEO}$	$I_C = 10.0 \text{ mA}, I_B = 0$	15	---	V dc
$BV_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	15	---	V dc
$BV_{EBO}$	$I_E = 10 \mu\text{A}, I_C = 0$	4.5	---	V dc
$h_{FE}$	$I_C = 10 \text{ mA dc}, V_{CE} = 1.0 \text{ V dc}$	30	150	---

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu\text{s}$ , duty cycle less than 2%.*